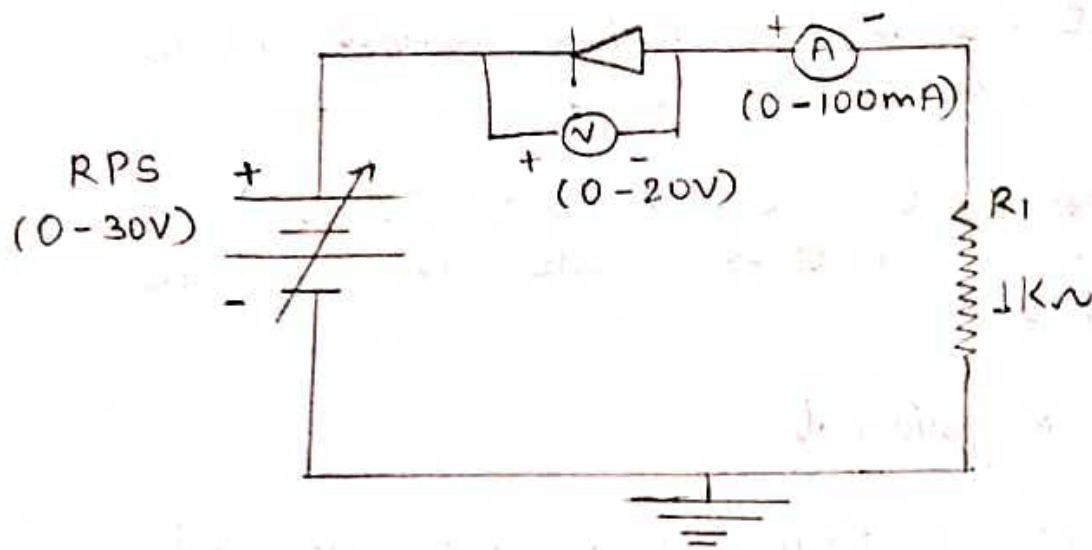
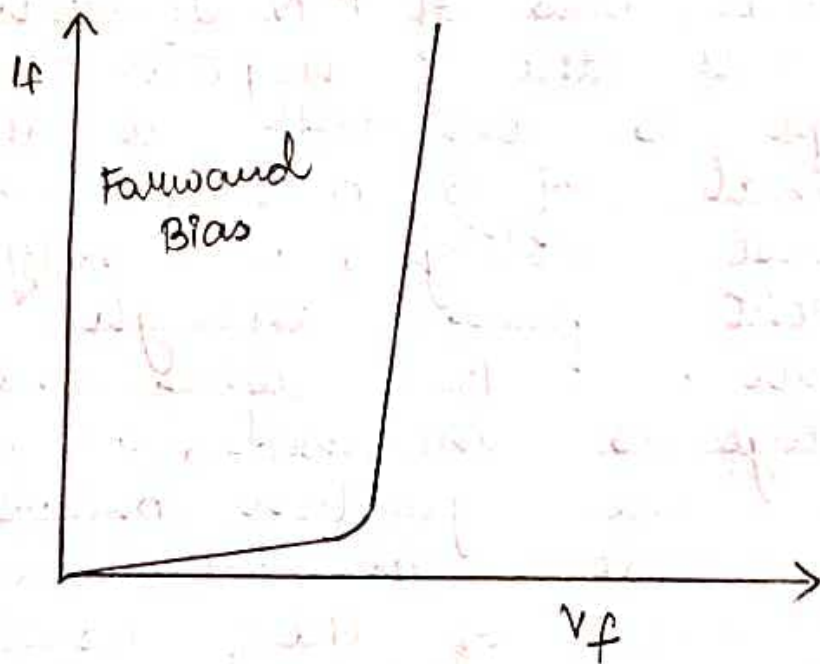


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PN Junction Forward Bias



Model graph for I-V characteristics

## 6. Characteristics of PN Junction diode under forward bias.

**AIM:-** To plot the characteristics curve of PN junction diode in forward bias.

### • Apparatus Required :

A diode, DC voltage supplier, Bread board,  $100\Omega$  resistor, two multi-meters for measuring current and voltage and connecting wires.

### • Procedure :

For the forward bias of a P-N junction, P-type is connected to the positive terminal while the N-type is connected to the negative terminal of a battery. The potential at P-N junction can be varied with the help of potential divider. At some forward ( $0.3V$  for Ge and  $0.1V$  for Si) the potential barrier is altogether eliminated and

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current starts flowing. This voltage is known as threshold voltage ( $V_{th}$ ) or cut in voltage or knee voltage. It is practically same as barrier voltage  $V_B$ . For  $V < V_{th}$ , the current is negligible. As the forward applied voltage increases beyond threshold voltage, the forward current rises exponentially.

### • Result

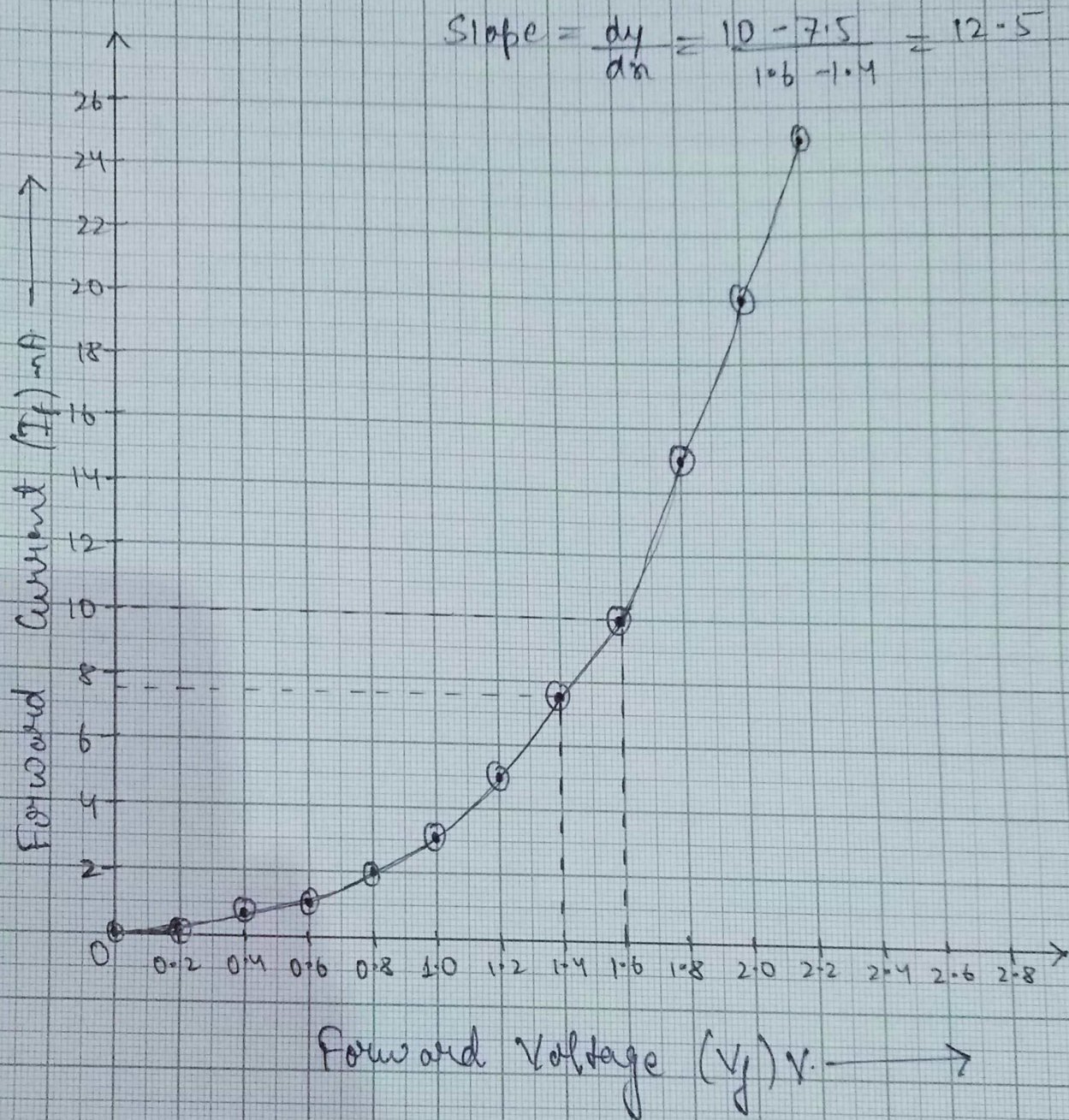
The forward bias I-V characteristic of PN junction diode is studied and curve is drawn.



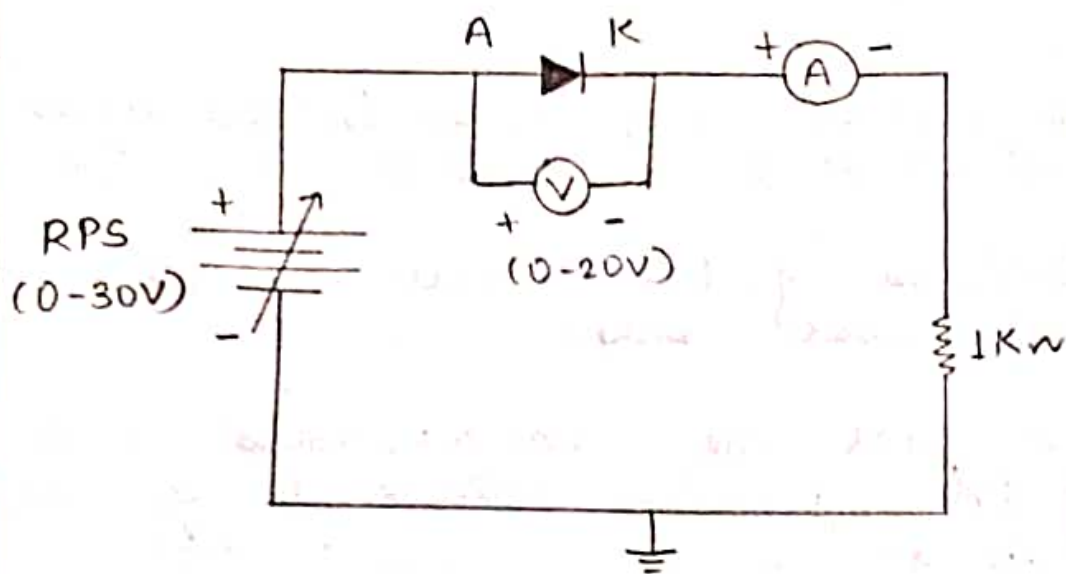
### Table

Characteristics of PN Junction diode under forward bias.

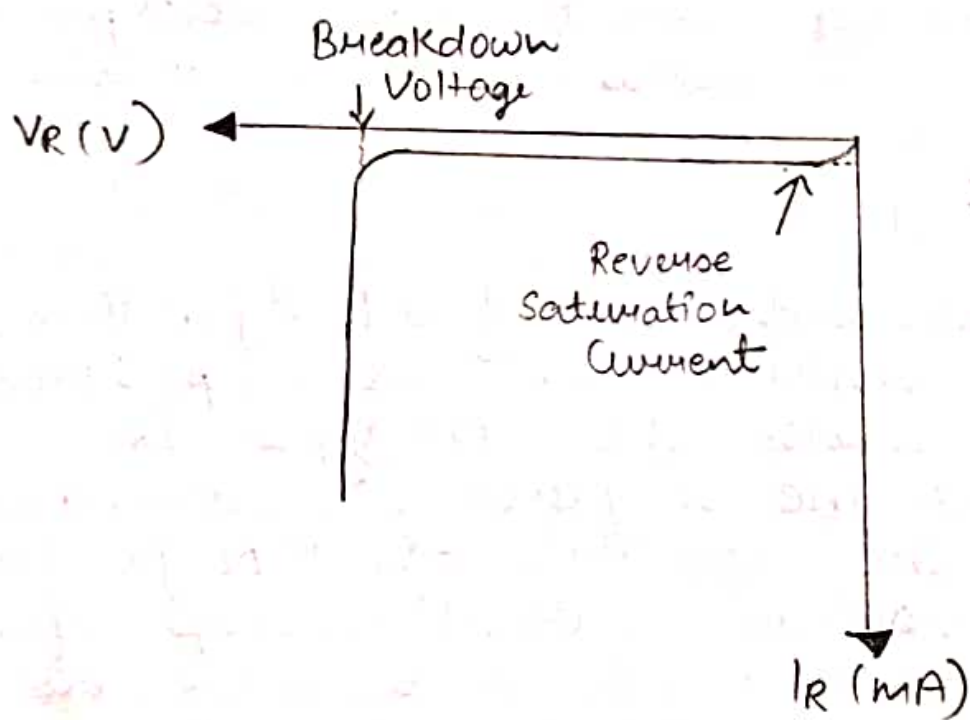
S.No.	Forward Voltage $V_f$	Forward current $I_f$
1	0	0
2	0.2	0
3	0.4	0.5
4	0.6	1
5	0.8	2
6	1.0	3
7	1.2	5
8	1.4	7.5
9	1.6	10
10	1.8	15
11	2.0	20
12	2.2	25







PN Junction Reverse Bias



Model graph for I-V characteristics.

### 6.b. characteristic of PN junction diode under reverse bias -

**AIM.** To plot the characteristic curve of PN junction diode in reverse bias.

#### • Apparatus

A diode, DC voltage supplier, Bread Board,  $100\Omega$  resistor, 2 multimeter for measuring current and voltage and connecting wires.

#### • Procedure

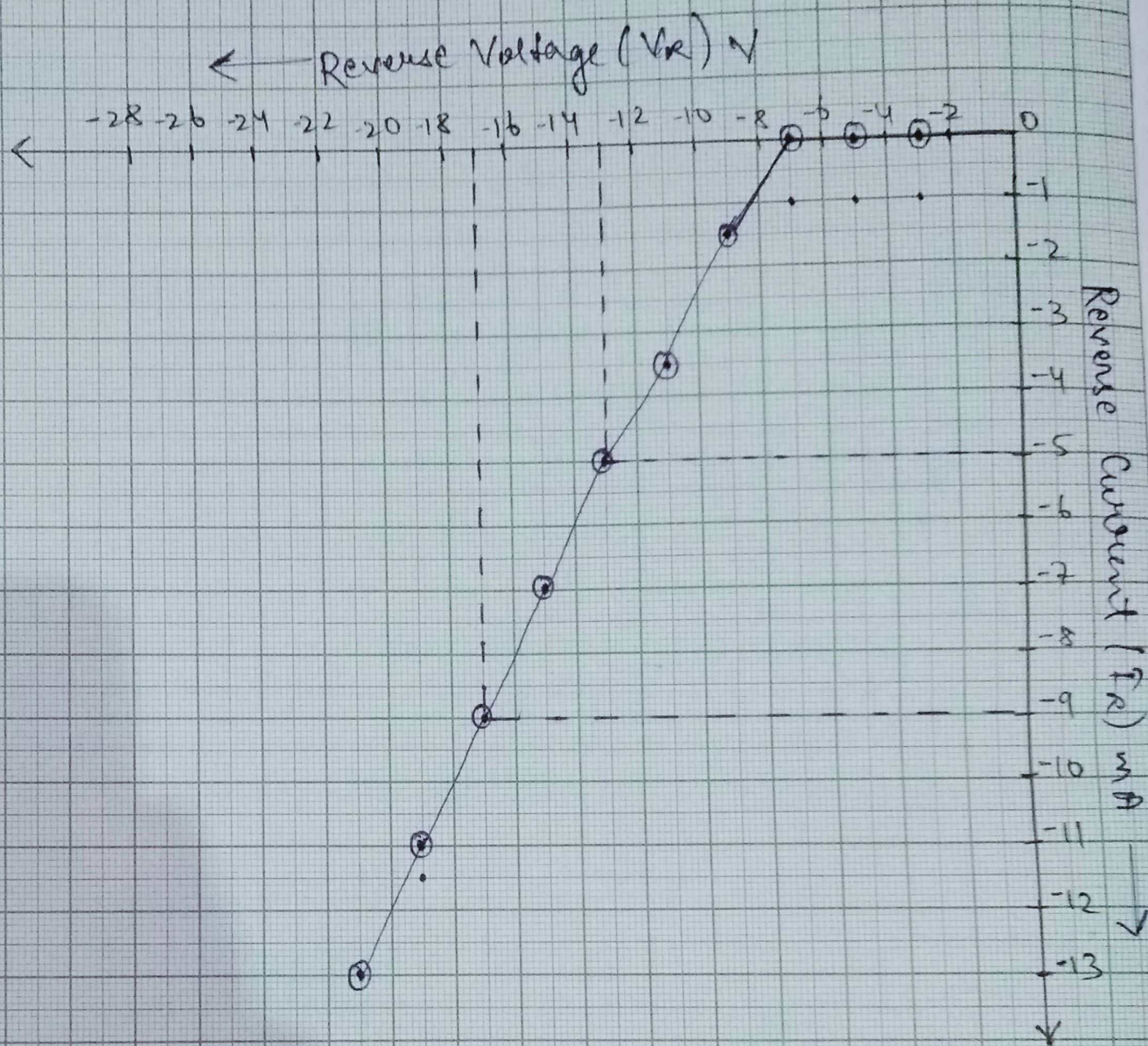
For the reverse bias of p-n junction, P-type is connected to the negative terminal while N-type is connected to the positive terminal of a battery. Under normal reverse voltage, a very little reverse current flows through a P-N junction. But when the reverse voltage is increased, a point is reached when the junction break down with sudden rise in reverse current. The critical value of the voltage is known as break down (VBR). The break down voltage is defined as the reverse voltage at which P-N junction breakdown with sudden rise in reverse current.

## Table

Characteristics of PN junction diode under reverse bias

S.No.	Reverse Voltage $V_R$	Reverse Current $I_R$
1	0	0
2	3	0
3	5	0
4	7	0
5	9	1.5
6	11	3.5
7	13	5
8	15	7
9	17	9
10	19	11
11	21	13





$$\text{Slope} = \frac{dy}{dx} = \frac{-9 - (-5)}{-17 - (-13)} = \frac{-4}{-4} = 1$$

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## • Result

The reverse bias I-V characteristic of PN junction diode is studied and curve is drawn.